MBR60L45CTG, MBR60L45WTG

Switch-mode Power Rectifier 45 V, 60 A

Features and Benefits

- Low Forward Voltage
- Low Power Loss/High Efficiency
- High Surge Capacity
- 175°C Operating Junction Temperature
- 60 A Total (30 A Per Diode Leg)
- Guard-Ring for Stress Protection
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

Applications

- Power Supply Output Rectification
- Power Management
- Instrumentation

Mechanical Characteristics:

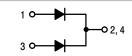
- Case: Epoxy, Molded
- Epoxy Meets UL 94 V-0 @ 0.125 in
- Weight (Approximately): 1.9 Grams (TO–220) 4.3 Grams (TO–247)
- Finish: All External Surfaces Corrosion Resistant and Terminal Leads are Readily Solderable
- Lead Temperature for Soldering Purposes: 260°C Max. for 10 Seconds
- Shipped 50 Units Per Plastic Tube for TO-220 and 30 Units Per Plastic Tube for TO-247



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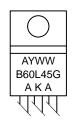
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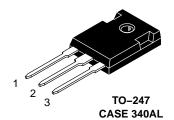
SCHOTTKY BARRIER RECTIFIERS 60 AMPERES, 45 VOLTS













B60L45 = Device Code A = Assembly Location

Y = Year
WW = Work Week
AKA = Polarity Designator
G = Pb-Free Device

ORDERING INFORMATION

Device	Package	Shipping
MBR60L45CTG	TO-220 (Pb-Free)	50 Units/Rail
MBR60L45WTG	TO-247 (Pb-Free)	30 Units/Rail

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MAXIMUM RATINGS (Per Diode Leg)

Rating	Symbol	Value	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V _{RRM} V _{RWM} V _R	45	V
Average Rectified Forward Current (Rated V_R) T_C = 145°C for MBR60L45CTG (Rated V_R) T_C = 165°C for MBR60L45WTG	I _{F(AV)}	30	А
Peak Repetitive Forward Current (Rated V _R , Square Wave, 20 kHz)	I _{FRM}	60	А
Nonrepetitive Peak Surge Current (Surge applied at rated load conditions halfwave, single phase, 60 Hz)	IFSM	200	А
Operating Junction Temperature (Note 1)	TJ	-65 to +175	°C
Storage Temperature	T _{stg}	-65 to +175	°C
Voltage Rate of Change (Rated V _R)	dv/dt	10,000	V/μs
ESD Ratings: Machine Model = C Human Body Model = 3B		> 400 > 8000	V

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

	Characteristic	Symbol	Value	Unit
Maximum Thermal Resistance (MBR60L45CTG) (MBR60L45WTG)	Junction-to-CaseJunction-to-Case	R _θ JC R _θ JC	1.9 0.59	°C/W

ELECTRICAL CHARACTERISTICS (Per Diode Leg)

Characteristic	Symbol	Value	Unit
Maximum Instantaneous Forward Voltage (Note 2) $ \begin{aligned} &(I_F=30~A,~T_C=25^\circ\text{C})\\ &(I_F=30~A,~T_C=125^\circ\text{C})\\ &(I_F=60~A,~T_C=25^\circ\text{C})\\ &(I_F=60~A,~T_C=125^\circ\text{C}) \end{aligned} $	VF	0.55 0.53 0.73 0.76	V
Maximum Instantaneous Reverse Current (Note 2) (Rated DC Voltage, T _C = 25°C) (Rated DC Voltage, T _C = 125°C)	i _R	1.2 275	mA

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions. 2. Pulse Test: Pulse Width = 300 μ s, Duty Cycle \leq 2.0%.

^{1.} The heat generated must be less than the thermal conductivity from Junction-to-Ambient: $dP_D/dT_J < 1/R_{\theta JA}$.

MBR60L45CTG, MBR60L45WTG

TYPICAL CHARACTERISTICS

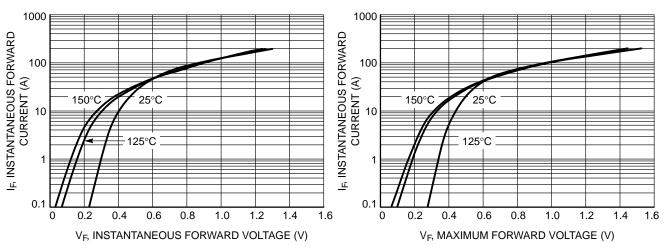


Figure 1. Typical Forward Voltage

Figure 2. Maximum Forward Voltage

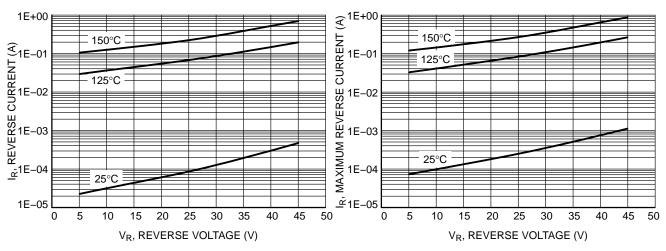


Figure 3. Typical Reverse Current

Figure 4. Maximum Reverse Current

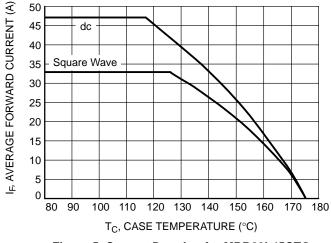


Figure 5. Current Derating for MBR60L45CTG

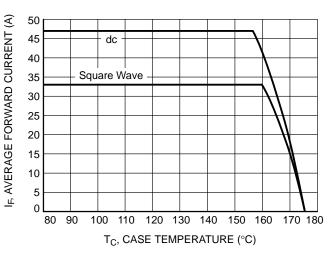


Figure 6. Current Derating for MBR60L45WTG

MBR60L45CTG, MBR60L45WTG

TYPICAL CHARACTERISTICS

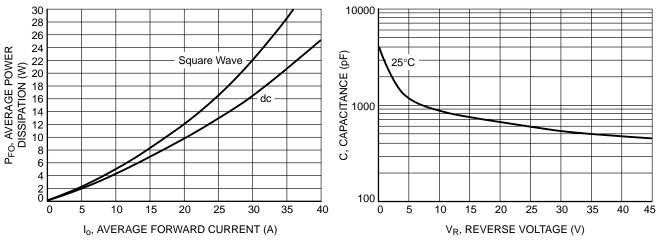


Figure 7. Forward Power Dissipation

Figure 8. Capacitance

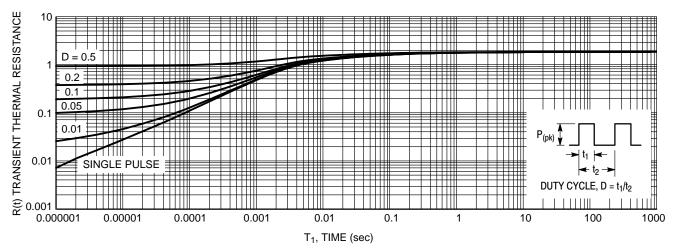


Figure 9. Thermal Response Junction-to-Case for MBR60L45CTG

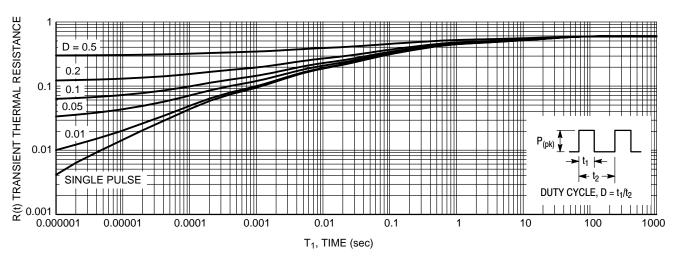
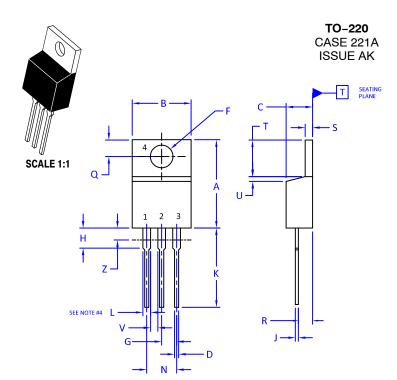


Figure 10. Thermal Response Junction-to-Case for MBR60L45WTG





DATE 13 JAN 2022

NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 2009.
- 2. CONTROLLING DIMENSION: INCHES
- 3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

4. MAX WIDTH FOR F102 DEVICE = 1.35MM

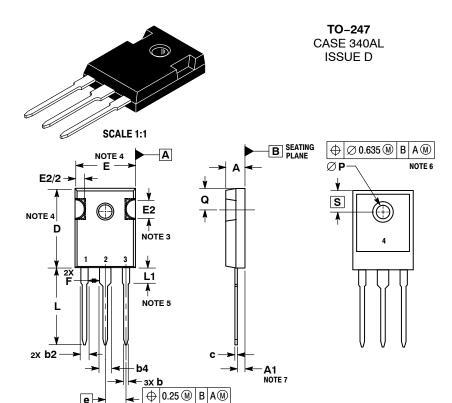
	INCHES		MILLIMETERS	
DIM	MIN.	MAX.	MIN.	MAX.
Α	0.570	0.620	14.48	15.75
В	0.380	0.415	9.66	10.53
С	0.160	0.190	4.07	4.83
D	0.025	0.038	0.64	0.96
F	0.142	0.161	3.60	4.09
G	0.095	0.105	2.42	2.66
Н	0.110	0.161	2.80	4.10
J	0.014	0.024	0.36	0.61
К	0.500	0.562	12.70	14.27
L	0.045	0.060	1.15	1.52
N	0.190	0.210	4.83	5.33
Q	0.100	0.120	2.54	3.04
R	0.080	0.110	2.04	2.79
S	0.045	0.055	1.15	1.41
Т	0.235	0.255	5.97	6.47
U	0.000	0.050	0.00	1.27
V	0.045		1.15	
Z		0.080		2.04

STYLE 1: PIN 1. 2. 3. 4.	COLLECTOR EMITTER	STYLE 2: PIN 1. 2. 3. 4.	COLLECTOR	STYLE 3: PIN 1. 2. 3. 4.	ANODE	2. 3.	MAIN TERMINAL 1 MAIN TERMINAL 2 GATE MAIN TERMINAL 2
STYLE 5: PIN 1. 2. 3. 4.	DRAIN SOURCE	STYLE 6: PIN 1. 2. 3. 4.	CATHODE ANODE	STYLE 7: PIN 1. 2. 3. 4.	ANODE	2. 3.	CATHODE ANODE EXTERNAL TRIP/DELAY ANODE
STYLE 9: PIN 1. 2. 3. 4.			GATE SOURCE DRAIN	STYLE 11: PIN 1. 2. 3. 4.		STYLE 12: PIN 1. 2. 3. 4.	MAIN TERMINAL 1 MAIN TERMINAL 2 GATE NOT CONNECTED

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DATE 17 MAR 2017

- NOTES:

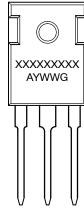
 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
 2. CONTROLLING DIMENSION: MILLIMETERS.
 3. SLOT REQUIRED, NOTCH MAY BE ROUNDED.

 - DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH.
 MOLD FLASH SHALL NOT EXCEED 0.13 PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTERMOST EXTREME OF THE PLASTIC BODY
- LEAD FINISH IS UNCONTROLLED IN THE REGION DEFINED BY
- ©P SHALL HAVE A MAXIMUM DRAFT ANGLE OF 1.5° TO THE TOP OF THE PART WITH A MAXIMUM DIAMETER OF 3.91.

 DIMENSION A1 TO BE MEASURED IN THE REGION DEFINED

	MILLIMETERS			
DIM	MIN	MAX		
Α	4.70	5.30		
A1	2.20	2.60		
b	1.07	1.33		
b2	1.65	2.35		
b4	2.60	3.40		
С	0.45	0.68		
D	20.80	21.34		
Е	15.50	16.25		
E2	4.32	5.49		
е	5.45 BSC			
F	2.655			
L	19.80	20.80		
L1	3.81	4.32		
P	3.55	3.65		
Q	5.40	6.20		
S	6.15 BSC			

GENERIC MARKING DIAGRAM*



XXXXX = Specific Device Code Α = Assembly Location

Υ = Year WW = Work Week = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking.

Pb-Free indicator, "G" or microdot " ■", may or may not be present.

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